

HMC788A Die Revision, Assembly Site and Material Change



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Detailed Change Description

Commercial Part

Parameter	Current	GoTo
Die rev. – via removal	No	Yes
Assembly Site	Unisem (UG1)	AEK
Lead Frame	100Sn	Ni-Pd-Au
Die Attach	Sumitomo CRM 1076DJ conductive	Hitachi EN 4900GC conductive
Mold Compound	Sumitomo G770HCD	Sumitomo G700LYT
Wire diameter (mils)	1.0	0.8



QUALIFICATION PLAN / STATUS					
TEST	SPECIFICATION	SAMPLE Size	RESULTS		
Low Temperature Storage (LTS)	JEDEC JESD22- A119	77	Pass		
Temperature Cycle (TC)*	JEDEC JESD22-A104	350	Pass		
High Temperature Storage Life (HTSL)	JEDEC JESD22-A103	154	Pass		
Solder Heat Resistance (SHR)*	JEDEC/IPC J-STD-020	375	Pass		
Electrostatic Discharge Human Body Model	ESDA/JEDEC JS-001	3/voltage	Pass <u>+</u> 750V		
Electrostatic Discharge Field-Induced Charged Device Model	JEDEC JESD22-C101	3/voltage	Pass <u>+</u> 1000V		

Qualification Results Summary of LFCSP at ASE (AEK)

* These samples were subjected to preconditioning (per J-STD-020 Level 3) prior to the start of the stress test. Level 3 preconditioning consists of the following: Bake: 24 hrs @ 125°C, Unbiased Soak: 192 hrs @ 30°C, 60%RH, Reflow: 3 passes through an oven with a peak temperature of 260°C.

Qualification Results Summary of 0.5µm GaAs PHEMT at WinSemi

QUALIFICATION RESULTS					
TEST	SPECIFICATION	SAMPLE SIZE	RESULTS		
High Temperature Operating Life (HTOL)	JEDEC JESD22-A108	185	Pass		
High Temperature Storage Life (HTSL)	JEDEC JESD22-A103	749	Pass		